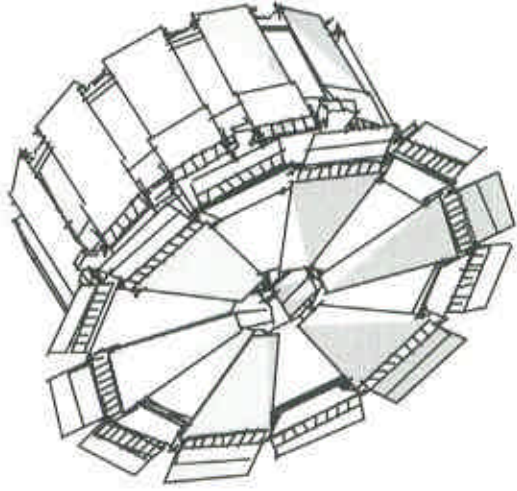


The DØ Silicon Vertex Detector

- ◆ Presented by Petros A. Rapidis, Fermilab on behalf of the DØ SMT group and the whole collaboration
- Emphasis on present status, testing, problems, ...

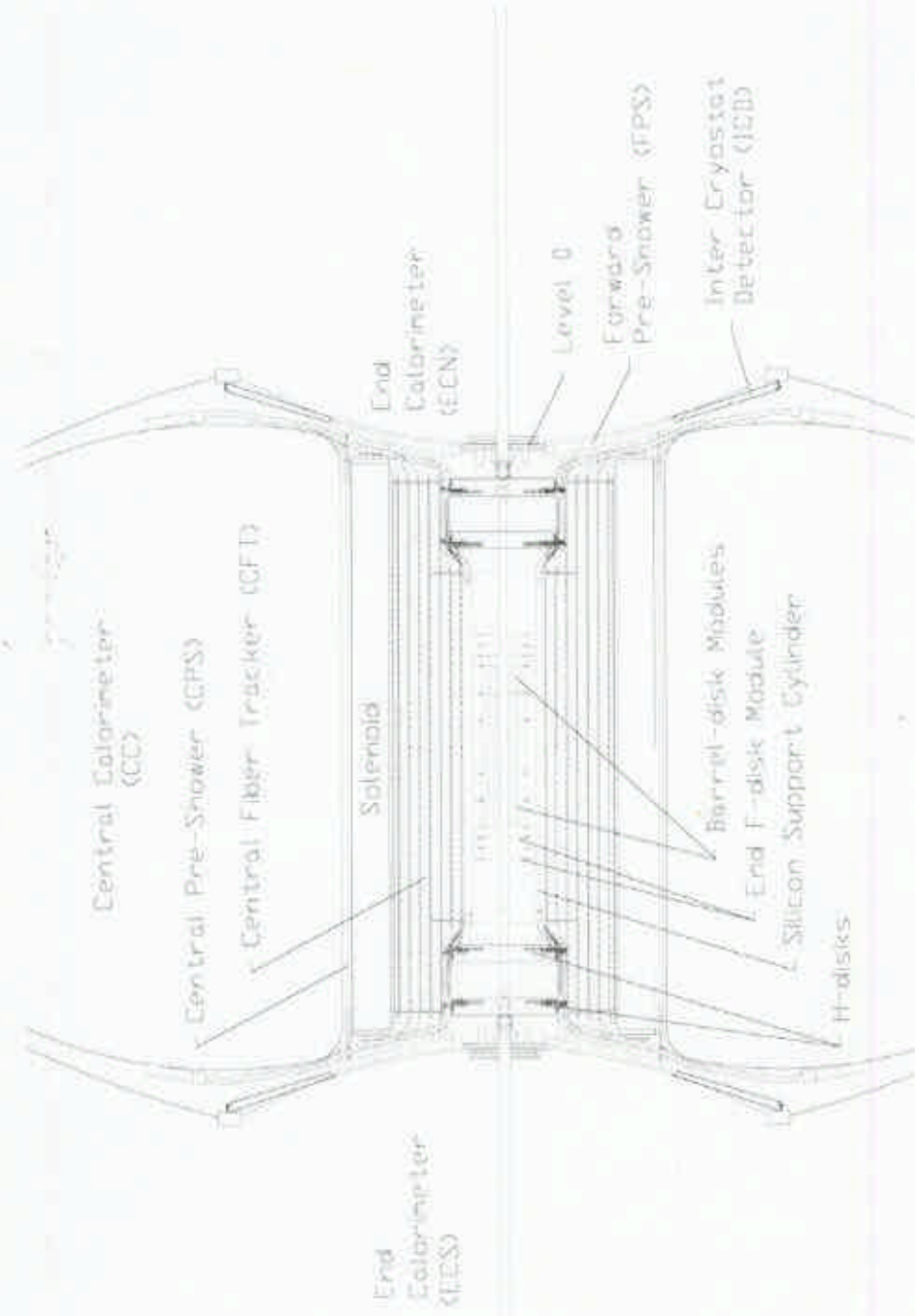


XXX ICHEP Osaka, July 2000

Physics Requirements for the DØ Silicon Detector

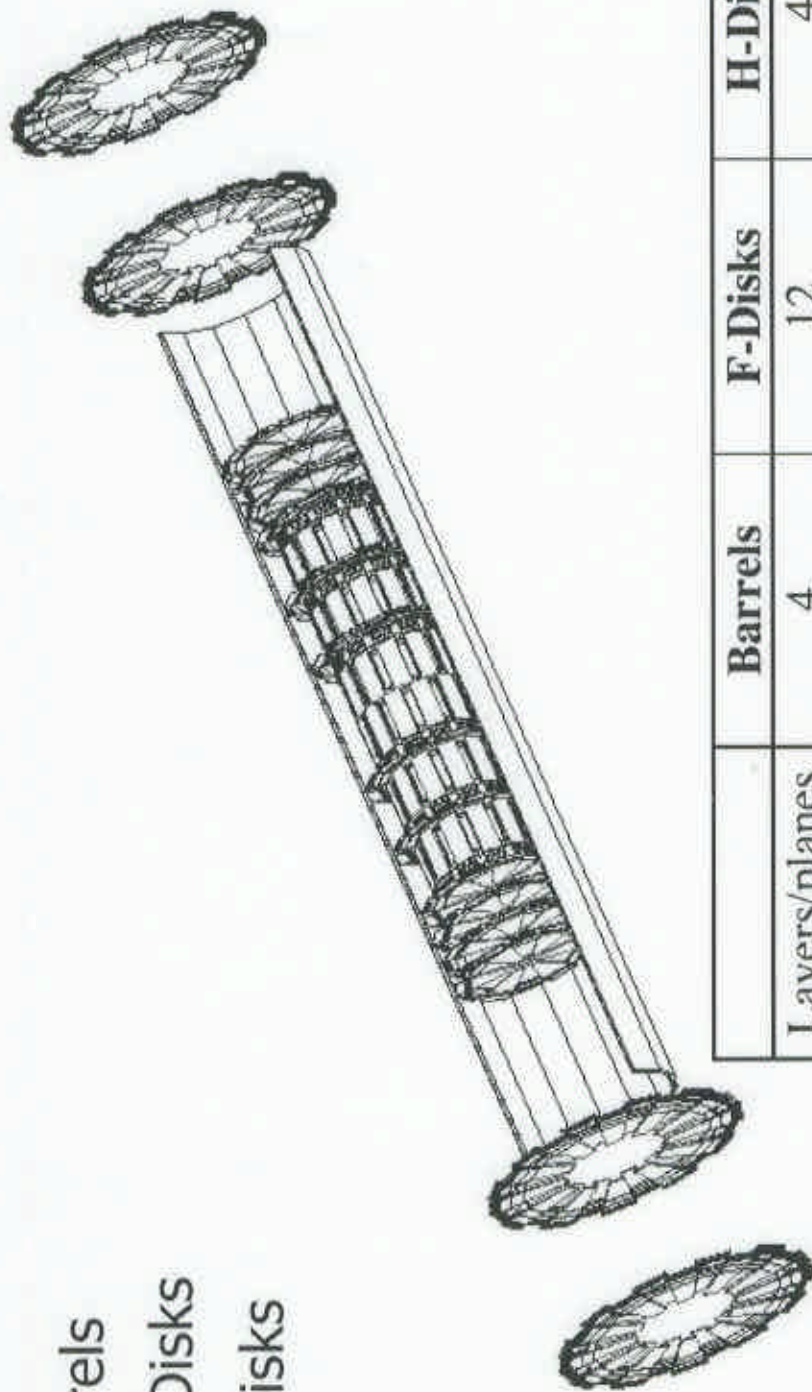
- ◆ Top physics, EW physics, Higgs searches, and physics beyond the Standard Model
 - Good performance for tracks with high p_T in $|\eta| < 3$; good performance for jets
- ◆ B physics
 - good performance for tracks with low p_T in $|\eta| < 3$.
- As small as possible a number of dead and noisy channels;
- Small impact of alignment to the detector resolutions;
- Allow for proper operation of the STT
- Small inefficiency and fake hit rate
- Resistant to radiation.

The DØ Upgrade Tracker



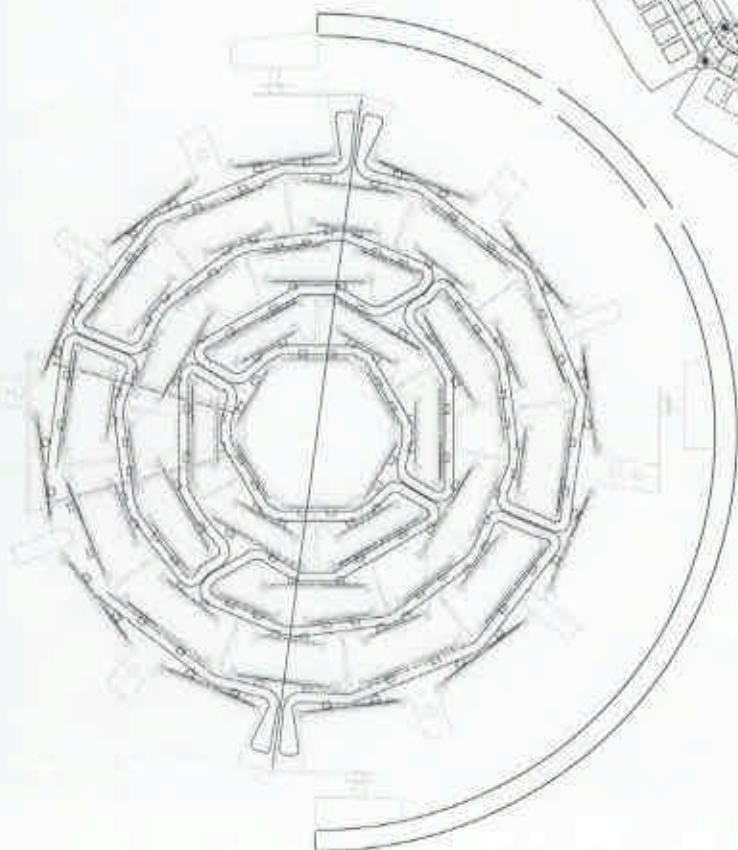
Silicon Microstrip Tracker

- ◆ 6 Barrels
- ◆ 12 F-Disks
- ◆ 4 H-Disks



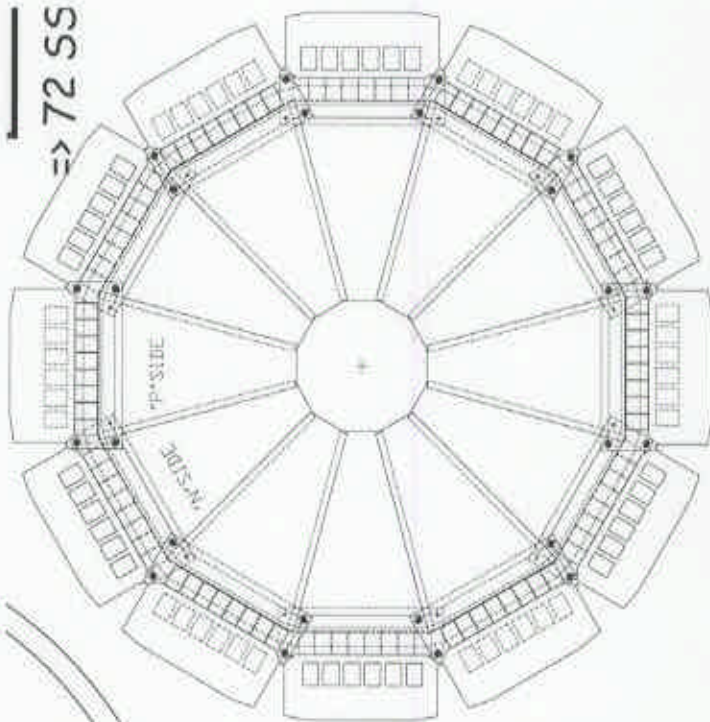
	Barrels	F-Disks	H-Disks
Layers/planes	4	12	4
Readout Length	12 cm	7.5 cm	14.6 cm
Inner Radius	2.7 cm	2.6 cm	9.5 cm
Outer Radius	9.4 cm	10.5 cm	26 cm

Cross sectional view



	B1&B6 (large z)	B2-B5 (small z)
Lr 1	12 SS	12 DS_90°
Lr 2	12 DS_2°	12 DS_2°
Lr 3	24 SS	24 DS_90°
Lr 4	24 DS_2°	24 DS_2°

=> 72 SS - 144 DS_90° - 216 DS_2°



A formidable task

- A vertex detector whose size is intermediate (I.e. a geometrical mean) between past silicon detectors and the future ones (LHC).

SIX BARREL DESIGN												
	F	H	_1-SS_1-D ϵ	L2	L3-SS_L3-D ϵ	L4	TOTAL					
# detector sides	2	1	1	2	1	2						
# detectors (total)	144	384	48	48	96	96	1248	<-	pieces of sili			
# IC's	2016	1152	72	288	144	576	6192	<-	SVX2E Chips			
# Kchannels	258	147	9.2	37	82.9	18.4	73.7	165.9	<-	Channels		
module count	144	192	24	48	72	48	96	144	<-	Ladders		
silicon area	3977	12586	611	1221	2661	1221	2442	5322	<-	wafer area		
wire bonds/module	4	4	4	4	6	4	4	6		Total wire bonds		
bias wire bonds	576	768	96	192	432	192	384	864		3504	1574400	
HDI count	288	192	24	48	72	48	96	144		912		
Total HV Pods	288	192	24	96	144	48	192	288		1272		
Total HV modules	72	48	6	24	36	12	48	72		318		

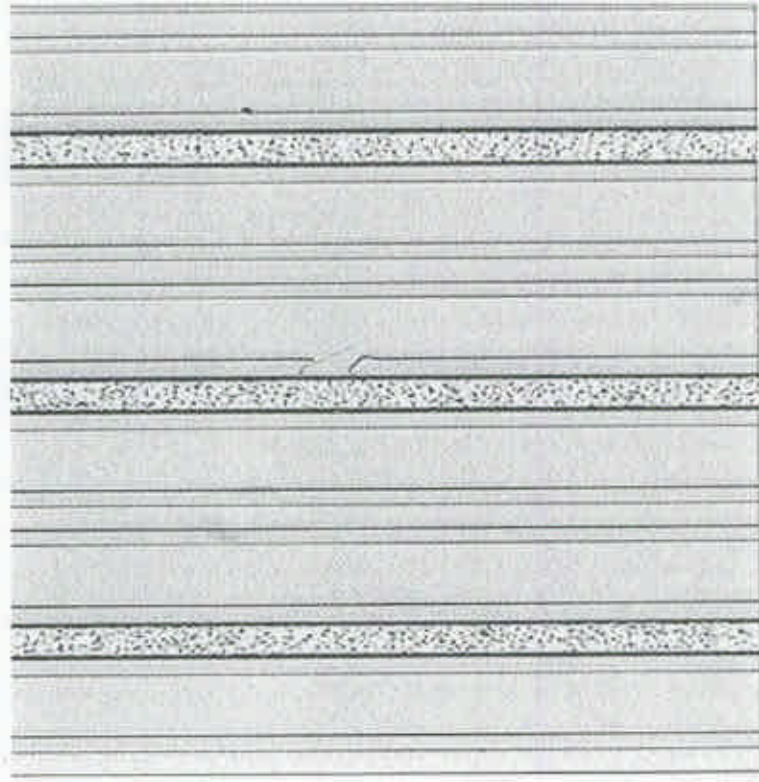
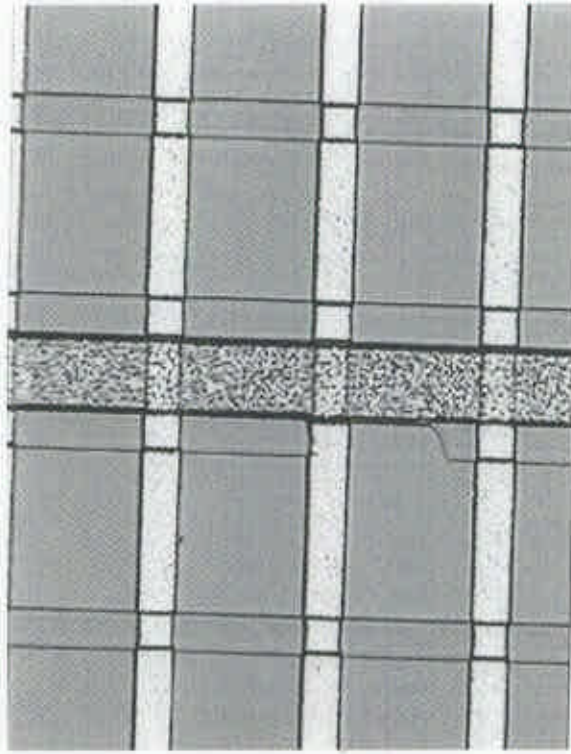


Overview of testing

- ◆ Sensors are probe tested for bad strips (broken capacitors), proper V-I characteristics, and adequate V_{depl}
- ◆ Sensors are assembled into detector modules (ladders or wedges) by gluing the electronics package on top of them (the HDI)
 - HDI's have been tested and burned in before hand
- ◆ Detectors are tested, burned-in, repaired, and finally tested with an IR laser on a traveling x-y gantry
- ◆ Detectors get tested again once they are mounted on a barrel
- ◆ They will be tested again as part of a larger assembly (e.g. the barrel and/or a disk).
 - Note the word that repeats all the time ...

Sensor Defects

- ◆ 144 90°-stereo barrel detectors (6-chip)-
problems
 - p-stop isolation defect on mask has led to low yield at the manufacturer (30%)

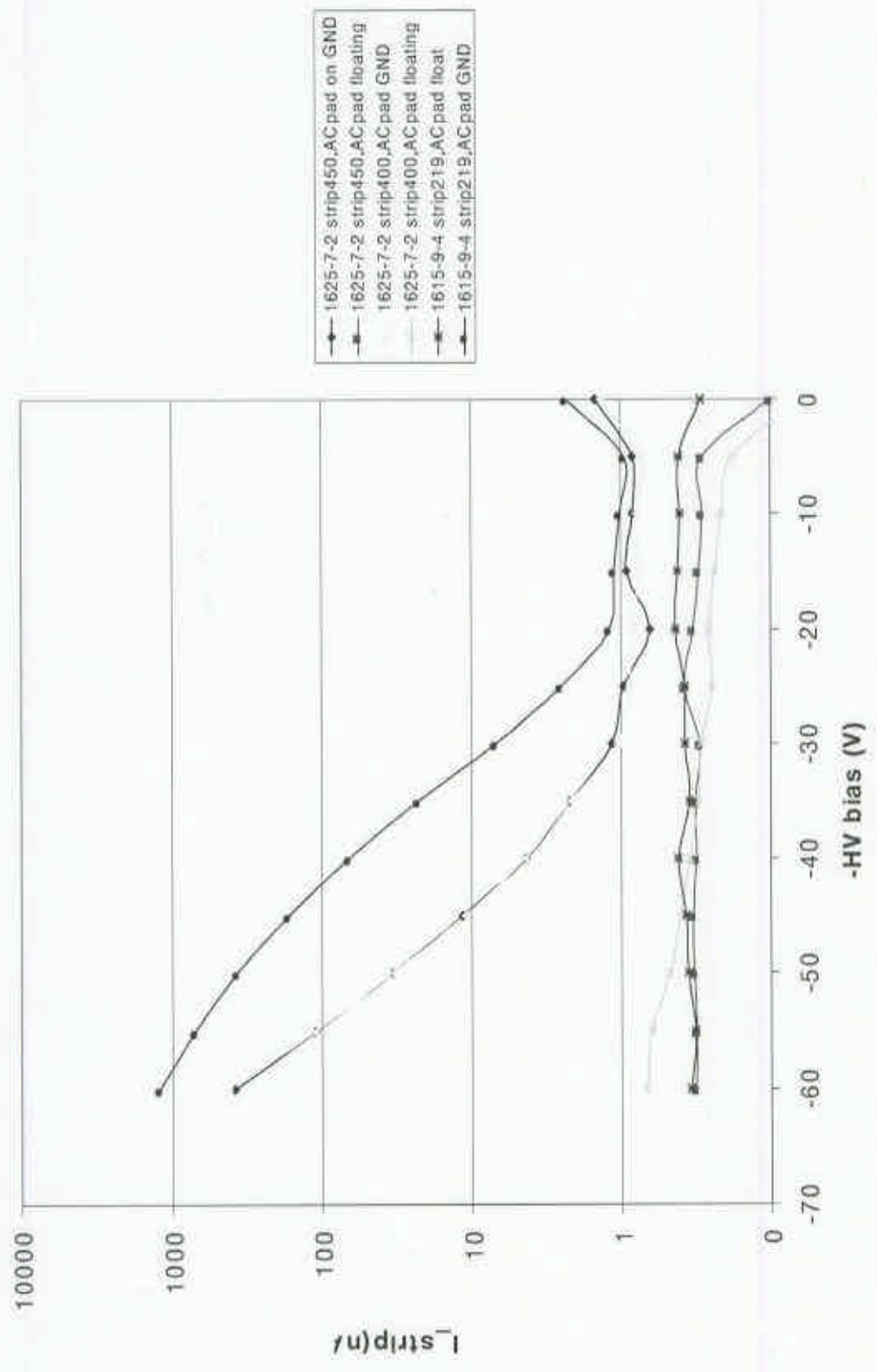


Microdischarges

- ◆ With positive bias (n side at ground, p side on negative potential) used to avoid large anomalous currents through shorted n-side coupling capacitors we observed a burst-like noise. Observation is consistent with microdischarges at the edge of strips (as seen by KEK group KEK 93-129).
- ◆ Steep increase in strip current if the coupling capacitor is grounded.
- ◆ Effect correlates with misalignment of Al-strips and implant
- ◆ Effect caused by field distortions and charge accumulation near the p-implant when p-side capacitor is grounded. Effect does not appear on the n+ strips
- ◆ We should expect that after irradiation and type inversion from n to p silicon the effect should disappear from the p side and move on to the n- side



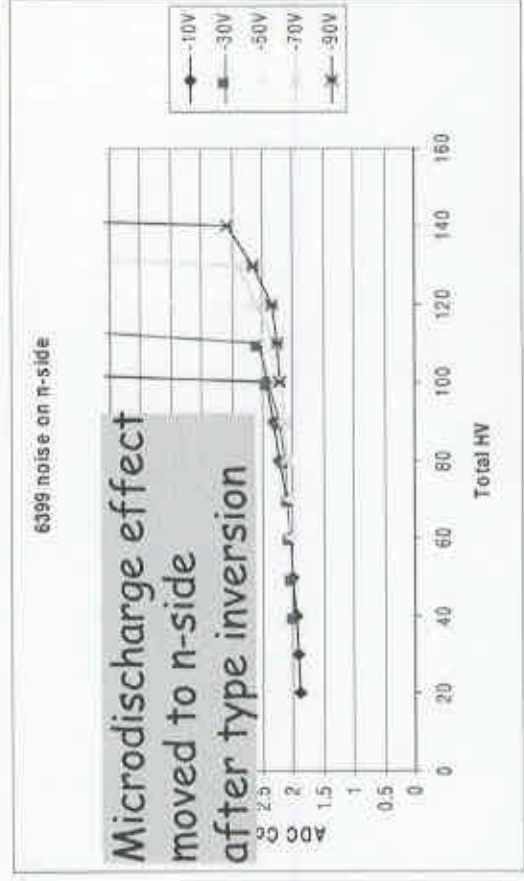
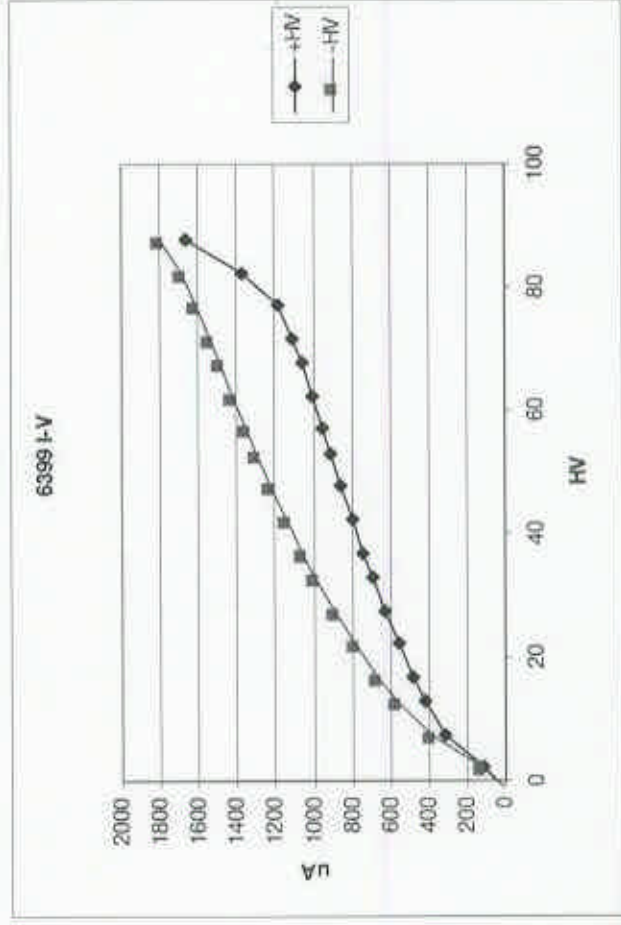
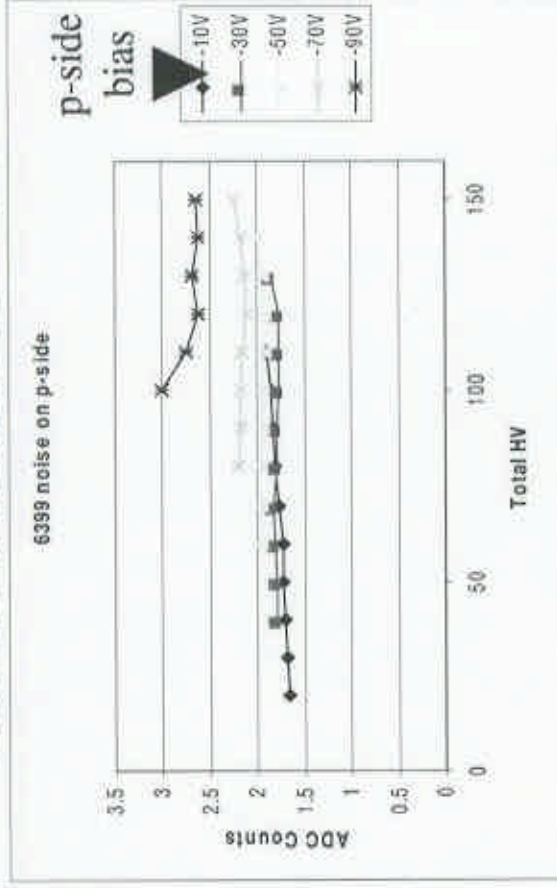
Microdischarges (cont)



Irradiated 90 degree detector

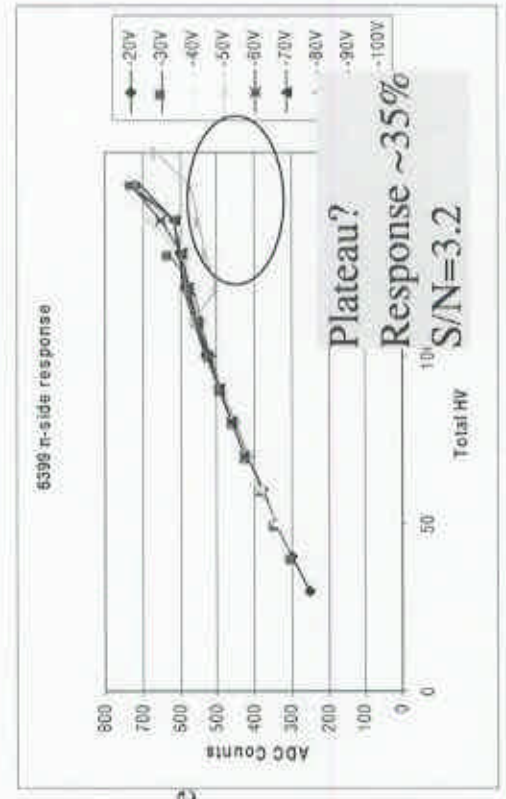
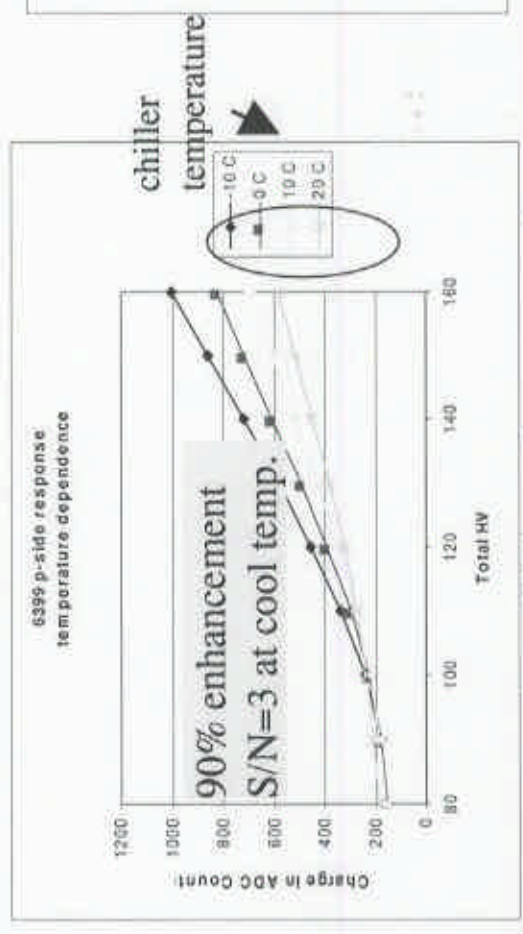
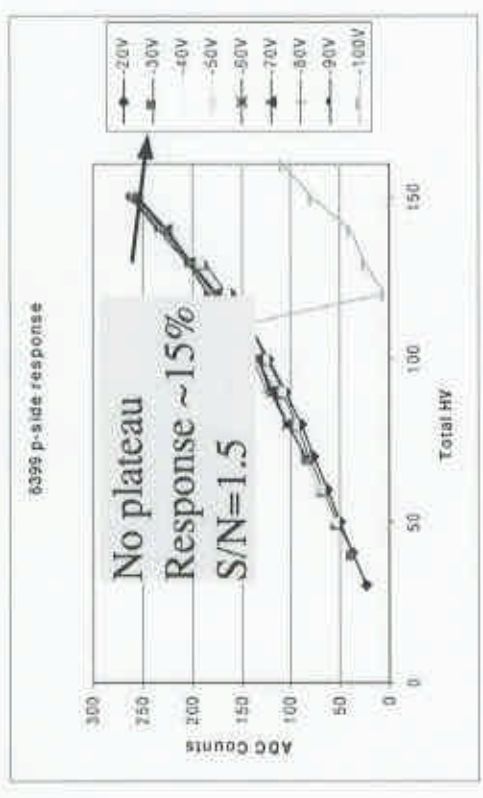
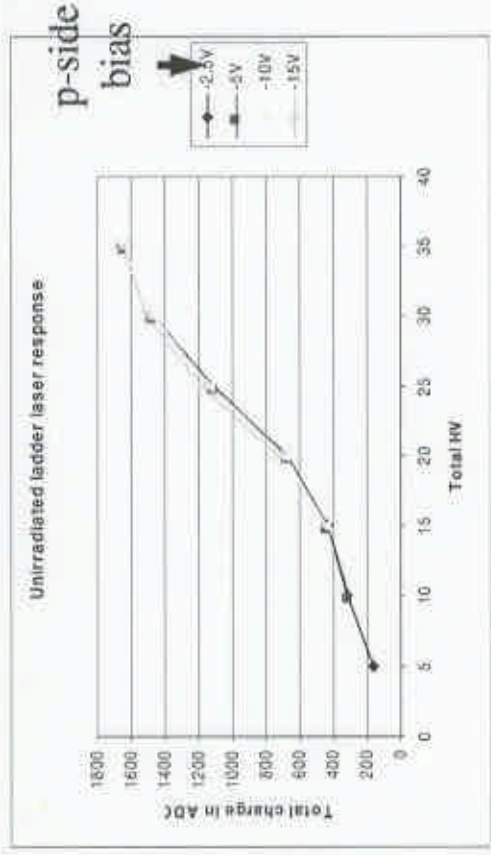
- 90 degree double-sided detector was irradiated with neutrons
 - Fluence: 1.0×10^{14} neutrons/cm²
 - 5 years of running for innermost layer
 - Type inverted
 - Kept at room temperature for 4 months for accelerated anti-annealing

- Noise level increase 30~40%



Response of Irradiated Detector

- ◆ Response to IR laser illumination

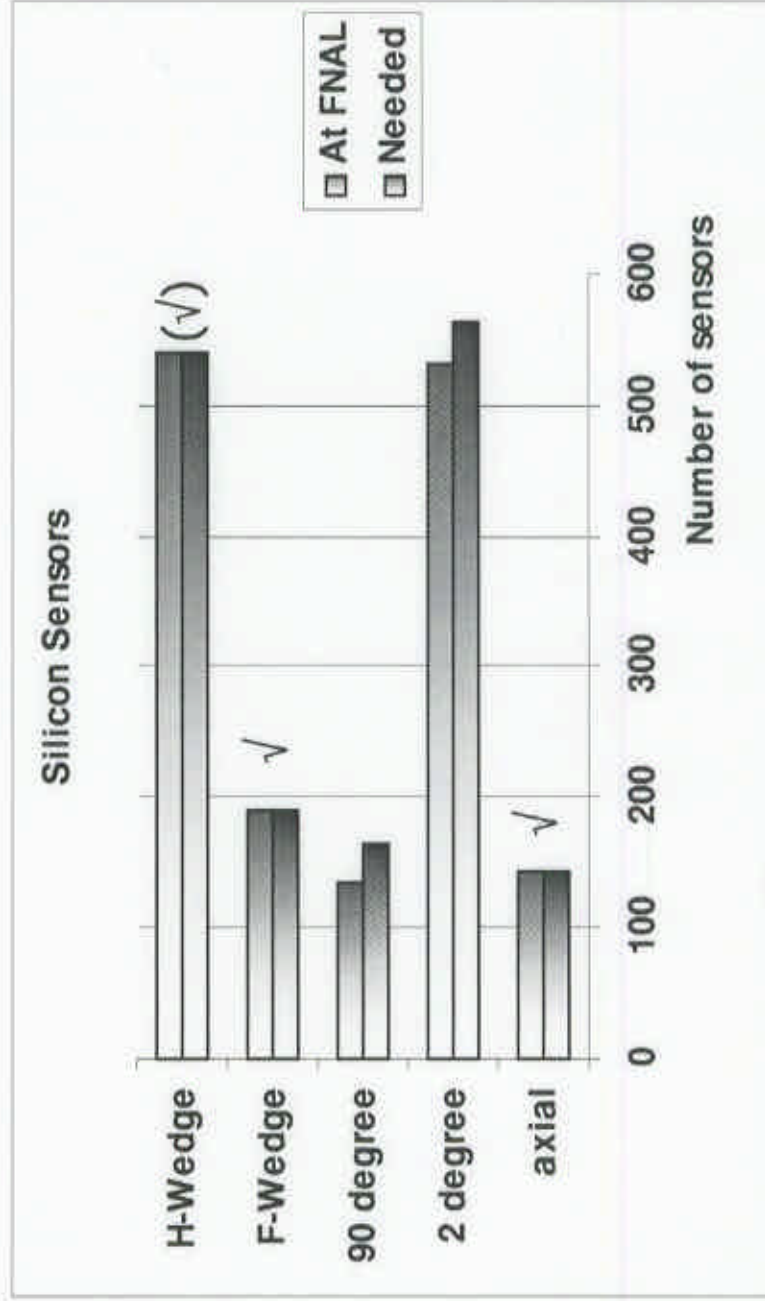


Charge collection efficiency increases at lower temperature
Detector is still usable after fluence of 10^{14} !



Sensor Delivery

A major problem that is (almost) behind us

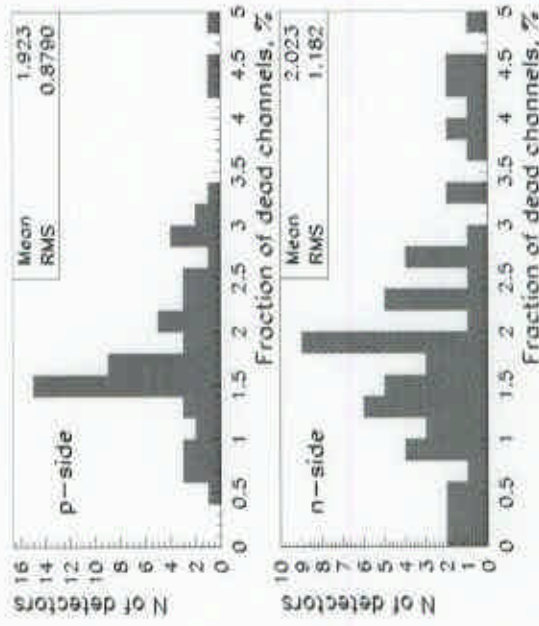


Overall Quality of the first half cylinder

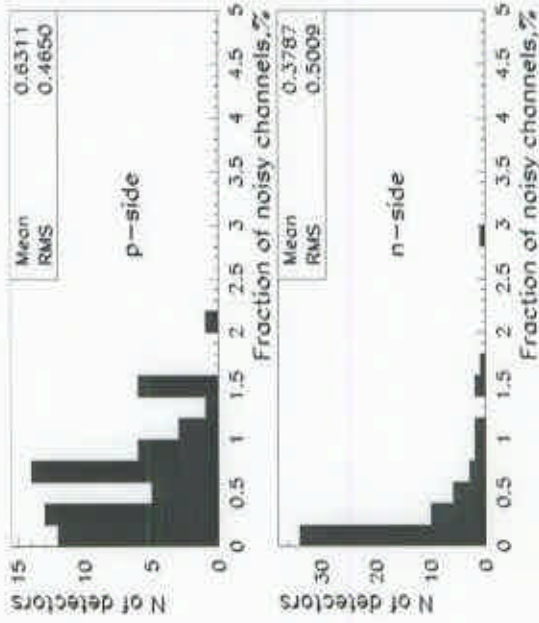
- ◆ Classification:
 - dead: laser response < 40 ADC counts
 - noisy: pedestal width > 6 ADC counts
 - A grade: < 2.6% dead/noisy channels
 - B grade: < 5.2% dead/noisy channels

9-Chip Ladders

Dead Channel Count



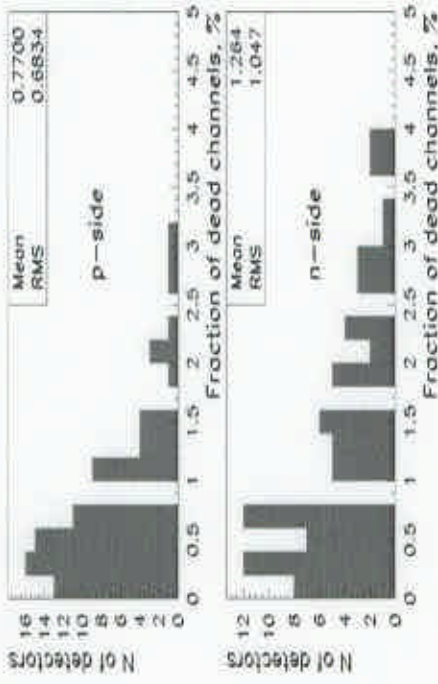
Noisy Channel Count



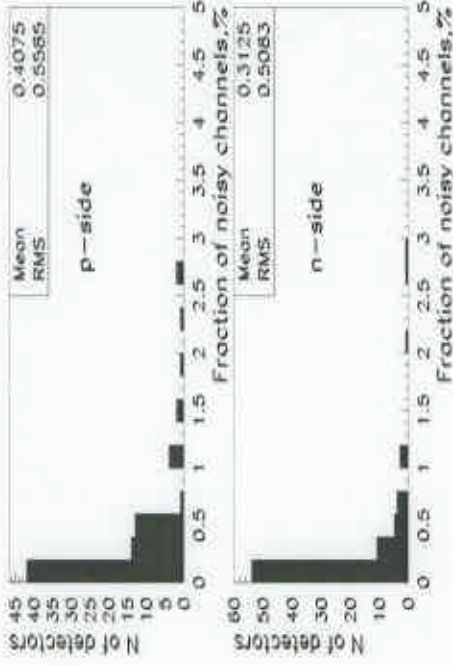
Overall quality of the first half cylinder (cont)

6-Chip Ladders

Dead Channel Count

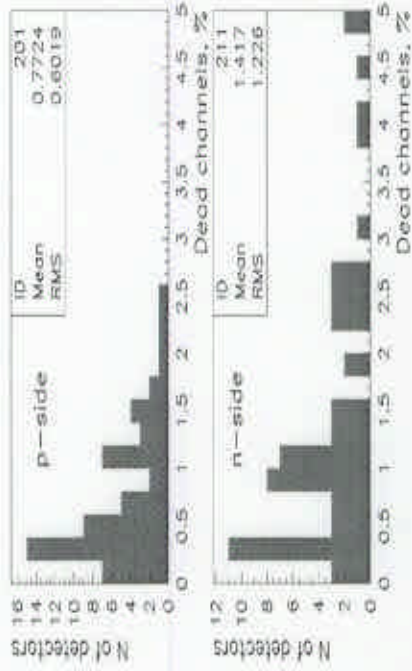


Noisy Channel Count

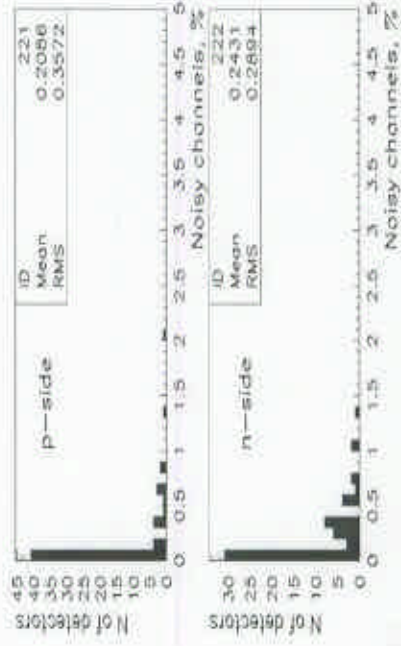


F Wedges

Dead Channel Count

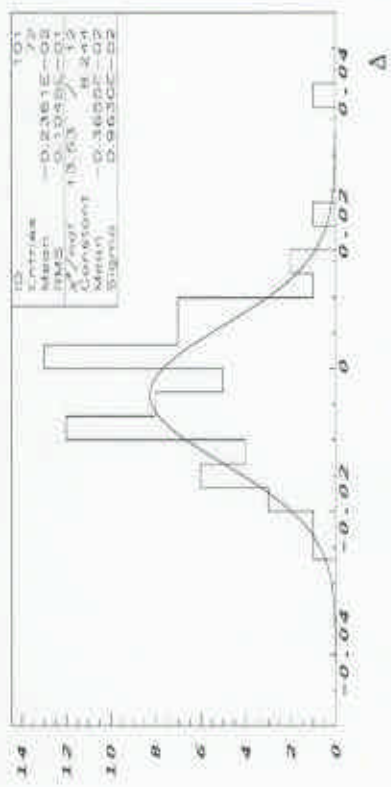


Noisy Channel Count



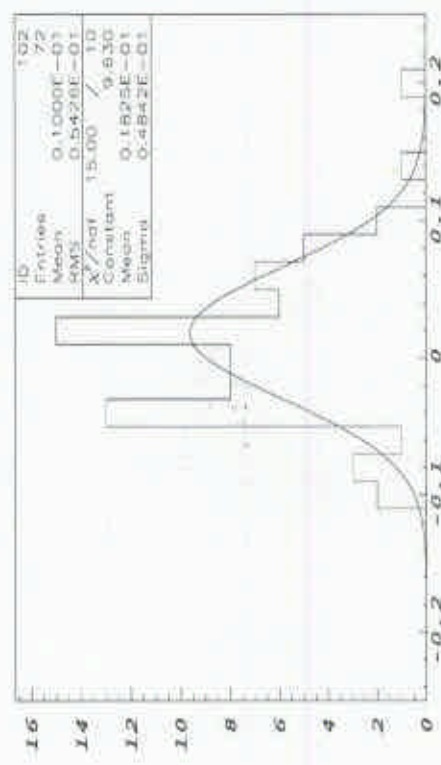
Barrel Alignment

→ Rotation in the ladder plane

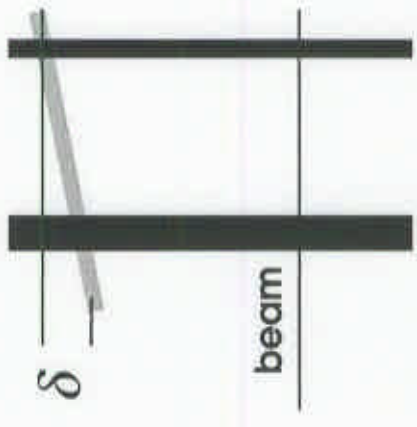


Δ of 10 microns induces error of 2.9 microns

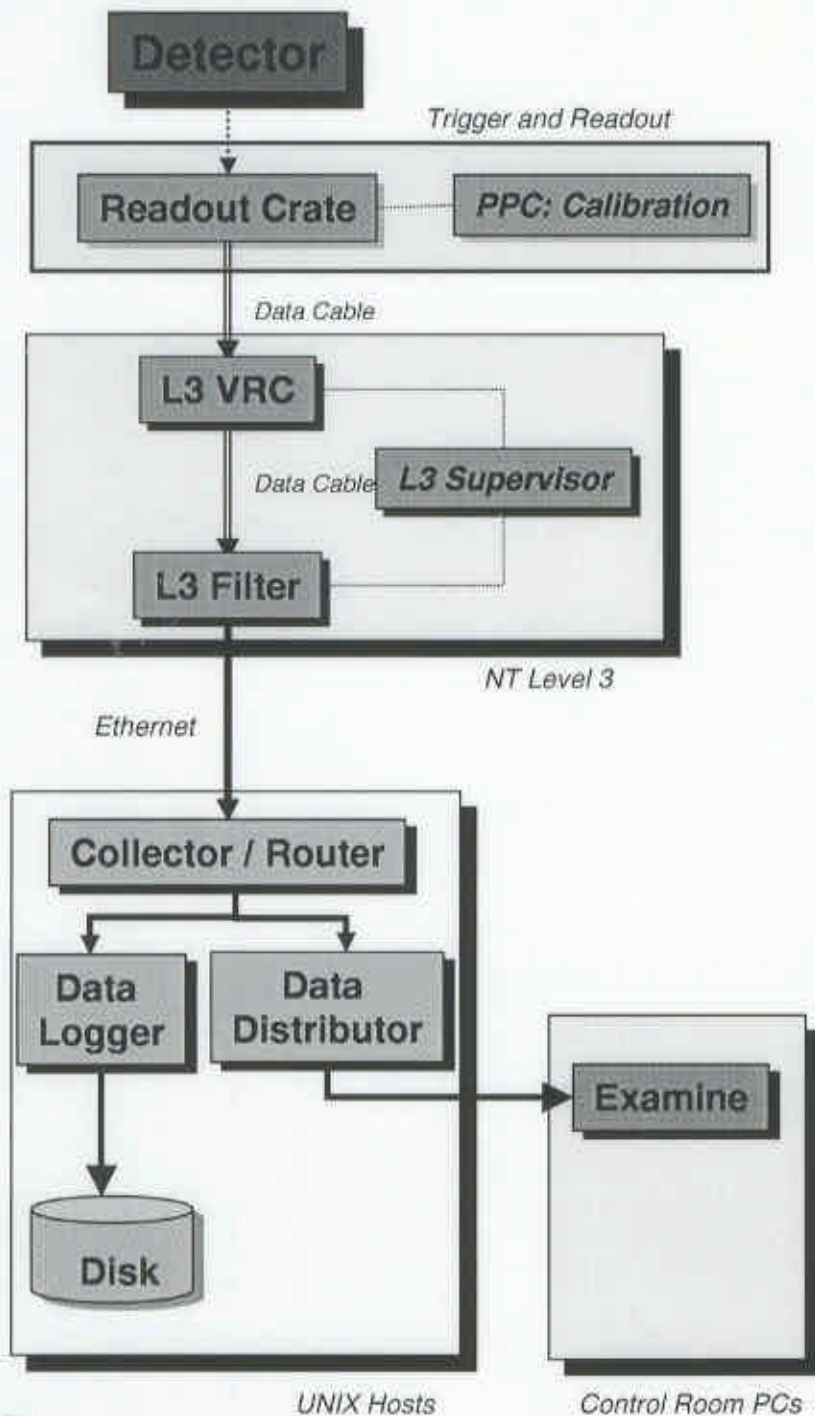
• Slope of the ladder with respect to beam



δ of 50 microns induces error of 3.3 microns in inner layers



Test of Full Readout System (July 14)

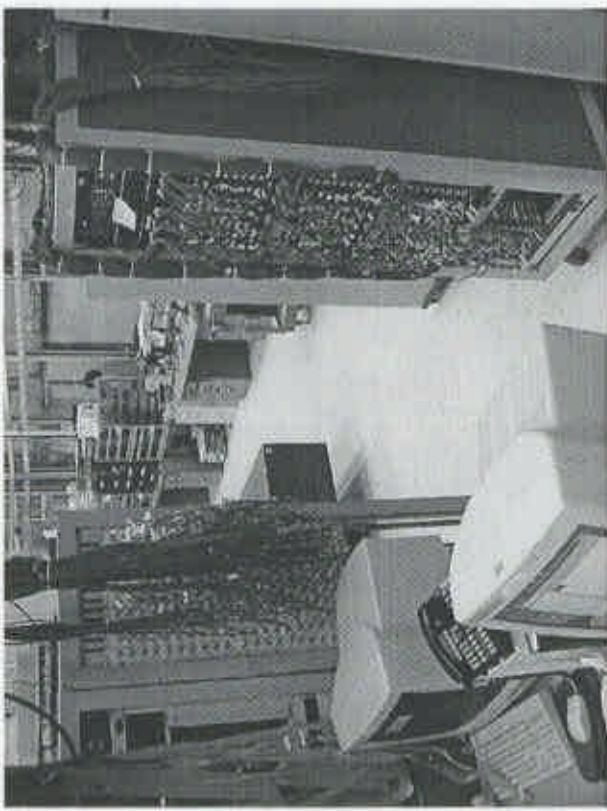
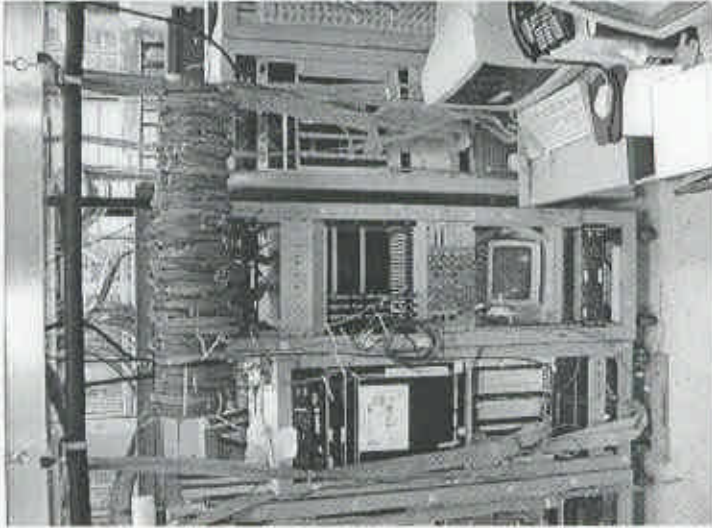
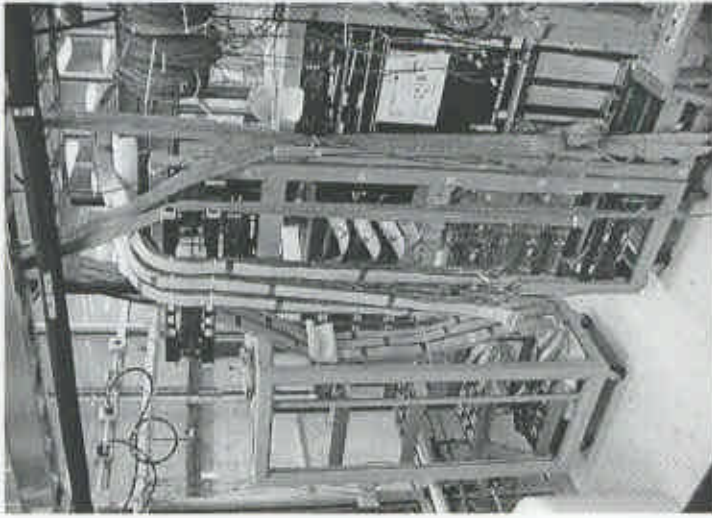


- Plan was to readout full F disk (F14) and exercise whole DAQ chain
- Instead, readout 3 hdi's
 - missing cooling, interlocks and some infrastructure

COOR controlled:

- Run Calibration in Front End
- Download parameters in Database
- Retrieve parameters from Database and download chips using proper protocol
- Start run
- Unpack and Analyze data in Level 3 node
- Ship data through collector / router to host
- Log data
- Store in SAM
- Analyze data online (Examine)

10 % System test



- To be used to test readout system, electronics integration, noise studies,
- Also to test larger detector assemblies (barrel/disk modules)
- And, to also do a cosmic ray study of a detector assembly



Petros Rapidis (FNAL)

Schedule, Lessons learned

- ◆ Presently 3 barrels and 6 F disks are ready
- ◆ First half cylinder being readied – expected in August
- ◆ Detector completed by the end of this year – we expect to be taking data by March 2nd, 2000
- ◆ This has been a much larger logistics enterprise than originally anticipated – design, procurement, construction, testing, and repairs all have taken much more effort than originally anticipated
- ◆ One should strive for a simple uniform design – too much variety is too much disruption
- ◆ Double sided silicon may not be worth it – the present thinking for the upgrade (to the upgrade!) envisions single sided silicon sensors glued back to back.